

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(base adj (conductor or contact)) near (doped adj semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:36
L2	28	(base adj (conductor or contact)) with (doped adj semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 13:14
L3	10	bicmos and ((base adj (conductor or contact)) near silicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 13:16
L4	12	bicmos and ((base near (conductor or contact)) near silicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 13:22
L5	0	"6803634".pn. and (polysilicon or silicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 13:23
L6	1	"6803634".pn. and (polycrystalline or silicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 13:27
L7	0	"6803634".pn. and silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 13:27
S1	914	257/370.ccis.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 09:03

S2	722	257/378.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 08:54
S3	354	257/517.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 08:55
S4	190	257/526.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 12:30
S5	615	257/552.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 08:57
S6	6	liang-minchang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 09:03
S7	4	liu-yow-juang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 09:04
S8	1	richter-fangyun.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 09:04